High Efficiency Silicon Rectifiers

Reverse Voltage - 100 to 1000 V
Forward Current 3 A

FEATURES

- For surface mounted applications
- Low profile package
- Open Junction chip
- Ideal for automated placement
- Lead free in comply with EU RoHS 2011/65/EU directives

MECHANICAL DATA

- Case: DO-201AD/ DO-27
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight:

Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.
Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	HER302	HER303	HER305	HER306	HER307	HER308	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at T_c = 100 °C	$I_{F(AV)}$	3.0						A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	I_{FSM}	15						
		0.95		1.25		1.65		

1 **Measured at 1 MHz and applied reverse voltage of 4 V D.C**

2 **Reverse recovery time test condition: IF=0.5A IR=1.0A Irr=0.25A**

FIG. 3-TYPICAL FORWARD VOLTAGE CHARACTERISTICS

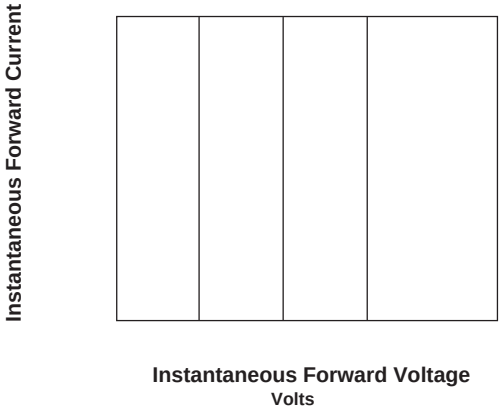
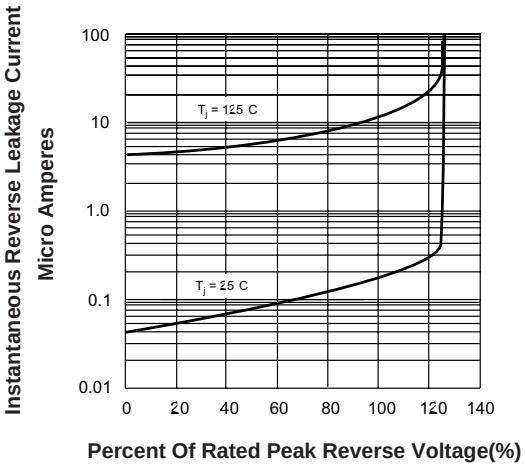


FIG. 4-TYPICAL REVERSE LEAKAGE CHARACTERISTICS



Ordering information

Package	Packing Description	Packing Quantity